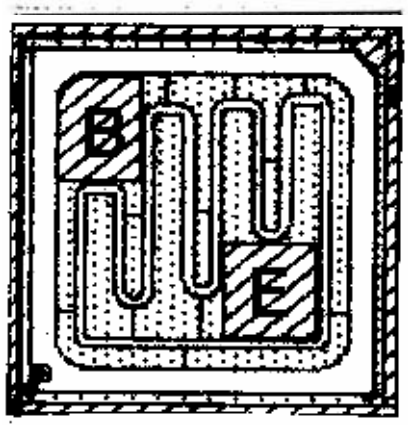
TIP32CM Chip For P-N-P Planar Power Transistor

General Description:
Silicon epitaxial chip of p-n-p medium power transistor (Ic max=3A)
used for general-purpose amplifier and switching application.
Complementary pair TIP31C

Wafer Diameter -- 100 mm
Wafer thickness -- 270 ± 20 μm;
Die size -- 1.7 x 1.7 mm ;

Metallization:
Top -- Al 4.5 ± 0.5 μm
Bottom -- Ti-Ni-Ag
Ti = 0.1 ± 0.02 μm
Ni = 0.5 ± 0.1 μm
Ag = 0.6 ± 0.1 μm

Bondpad size:
1. Base 0.4 x 0.3 mm
2.Emitter 0.312 x 0.312 mm



Recommended ultrasonic bonding wire Al
Emitter - 2 wire dia 80 μm
Base - 1 wire dia 80 μm

ELECTRICAL CHARACTERISTICS CHIPS ON WAFER (Ta=25°C)

Parameter	Symbol	Unit	Measurement Mode	Min	Max
Collector cutoff Current	Iceo	mA	Vce=**45V**; Ib=0		0.3
Collector cutoff Current	Ices	mA	Vce=**60V**; Ube=0		0.2
Emitter cutoff Current	Iebo	mA	Veb=5,0 V; Ic=0		1.0
Collector – Emitter Sustaining	Vceo (sus)	V	Ic=30 mA, Ib=0	**60**	
DC Current Gain(1) **	h_{FE}		Vce=4V; **Ic=1A**	**100**	
Small-Signal Current Gain **	h_{fe}		Vce=10V; Ic=0,5 A f=1kHz	20	
Collector-Emitter Saturation Voltage(1)	Vce(sat)	V	Ic=1A; **Ib=35mA**		0.5
Base- Emitter On Voltage(1) **	Vbe(on)	V	Vce=4 V; Ic=3 A		1.8

1.Pulse Tests: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2%
2.** In a circuit with common base Ucb= Uce-1v ; Ie=Ic